



VRM: 130 Volts

Izsm : 1.0 Amp. (100 ms)

FEATURES:

- * 600 W surge capability at 1ms
- * Excellent clamping capability
- * Low zener impedance
- * Fast response time : typically less than 1.0 ps from 0 volts to BV min.
- * Low Leakage < 5.0 μ A above 10 V.
- * Pb / RoHS Free

MECHANICAL DATA:

- * Case : D2 Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight: 0.465 gram

AVALANCHE DIODE



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Peak Power Dissipation at TP = 1 ms (Note 1)	Ppk	Minimum 600	W
Steady State Power Dissipation at TL = 75 °C			
Lead Lengths 0.375", (9.5mm) (Note 2)	Po	5.0	W
Working Peak Reverse Voltage (Stand-off Voltage)	Vrwm	130	V
Minimum Avalanche Breakdown Voltage at IT = 1mA (Note 3)	VBR(min)	135	V
Maximum Avalanche Breakdown Voltage at IT = 1mA (Note 3)	VBR(max)	180	V
Peak Forward Surge Current, 8.3 ms Single Half Sine-Wave	Ігѕм	75	А
Superimposed on Rated Load (JEDEC Method) (Note 4)			
Maximum Reverse Leakage at Working Peak Reverse Voltage	IR	5.0	μA
Maximum Non-Repetitive Peak Reverse Surge Current	IRSM	2.6	A
Maximum Reverse Voltage (Clamping Voltage) at IRSM	Vrsm	234	V
Maximum Voltage Temperature Variation of Breakdown Voltage		175	mV/°C
Junction Temperature Range	TJ	- 65 to + 175	°C
Storage Temperature Range	Tstg	- 65 to + 175	°C

Notes :

- (1) Non-Repetitive Current Pulse and Surge Current Waveform, per Fig. 6 and Derated above Ta = 25°C per Fig. 1.
- (2) Mounted on Copper Leaf area pf 1.57 in² (40 mm²)

(4) 8.3 ms single half sine-wave, duty cycle = 4 pulses per Minutes maximum.



⁽³⁾ VBR measured after IT applied for 300 μ s, IT = Square W ave Pulse or equivalent.





